

# 2SC5474 (Tentative)

Silicon NPN epitaxial planer type

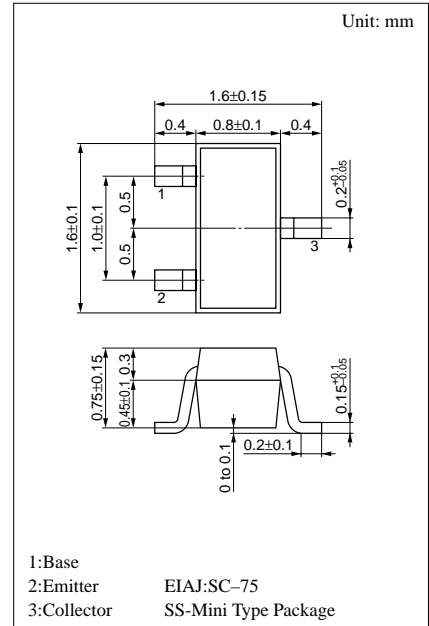
For low-voltage low-noise high-frequency oscillation

## Features

- High transition frequency  $f_T$ .
- High gain of 8.9dB and low noise of 1.8dB at 3V.
- Optimum for RF amplification of a portable telephone and pager.
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	9	V
Collector to emitter voltage	$V_{CEO}$	6	V
Emitter to base voltage	$V_{EBO}$	1	V
Collector current	$I_C$	30	mA
Collector power dissipation	$P_C$	125	mW
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55 ~ +125	°C

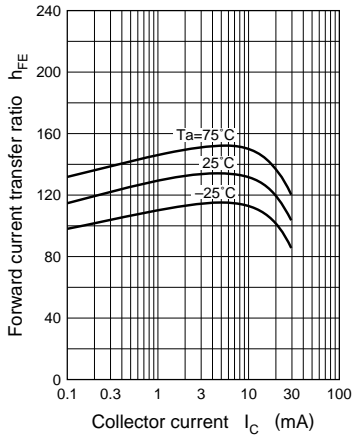


Marking symbol : 3A

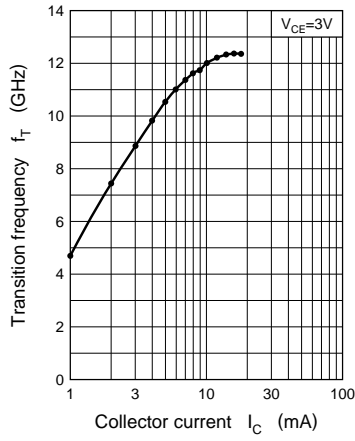
## Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 9V, I_E = 0$			1	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 1V, I_C = 0$			1	$\mu A$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 3V, I_C = 10mA$	80		200	
Collector output capacitance	$C_{ob}$	$V_{CB} = 3V, I_E = 0, f = 1MHz$		0.4		pF
Transition frequency	$f_T$	$V_{CE} = 3V, I_C = 10mA, f = 2GHz$		12.0		GHz
Noise figure	NF	$V_{CE} = 3V, I_C = 3mA, f = 1.5GHz$		1.8		dB
Forward transfer gain	$ S_{21e} ^2$	$V_{CE} = 3V, I_C = 10mA, f = 2GHz$		8.9		dB

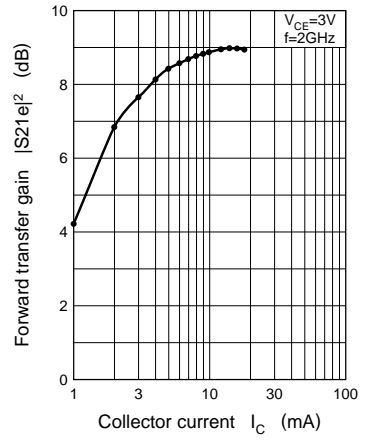
$h_{FE} - I_C$



$f_T - I_C$



$|S_{21e}|^2 - I_C$



NF -  $I_C$

